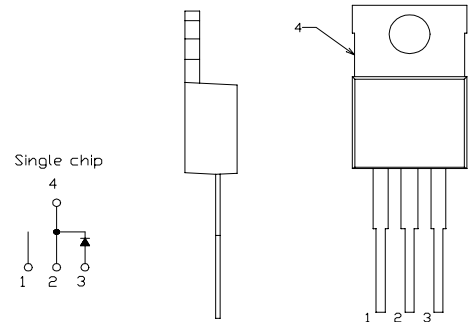


# FRD Type : GSF10A60B

## OUTLINE DRAWING

### FEATURES

- \* Similar to TO-220AB Case
- \* Ultra – Fast Recovery
- \* Low Forward Voltage Drop
- \* Low Power Loss, High Efficiency
- \* High Surge Capability
- \* 200 Volts thru 600 Volts Types Available



### Maximum Ratings

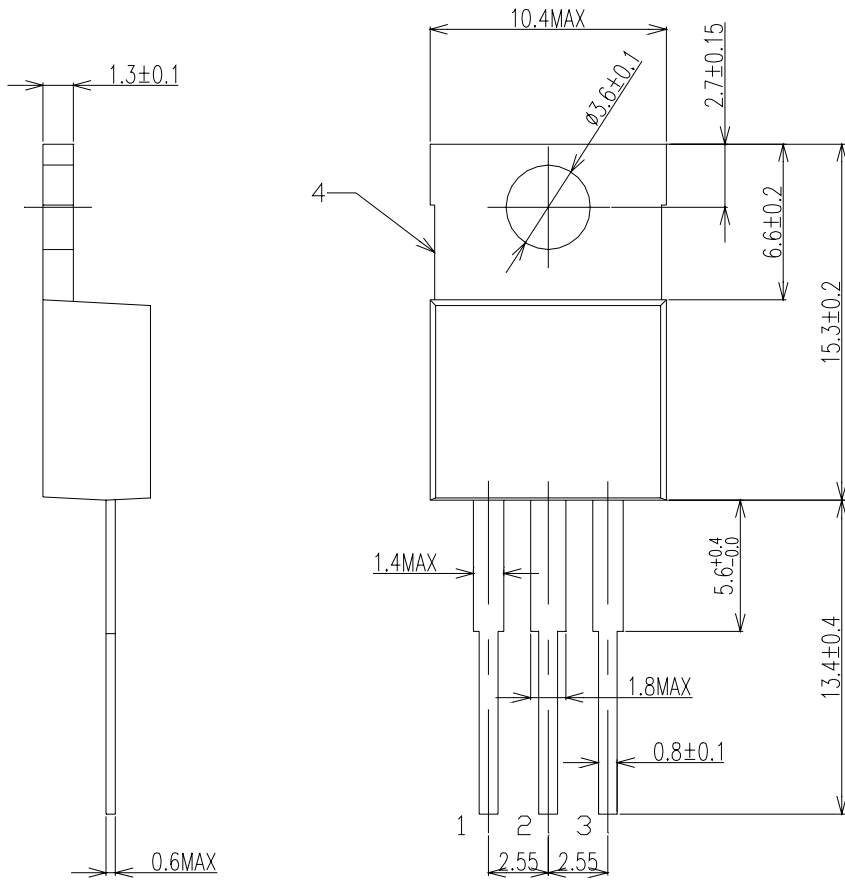
Approx Net Weight:1.9g

Rating	Symbol	GSF10A60B		Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	600		V
Average Rectified Output Current	$I_O$	10	$T_c=74^{\circ}C$ 50 Hz Half Sine Wave Resistive Load	A
RMS Forward Current	$I_{F(RMS)}$	15.7		A
Surge Forward Current	$I_{FSM}$	120	50 Hz Half Sine Wave, 1 cycle Non-repetitive	A
Operating Junction Temperature Range	$T_{jw}$	- 40 to + 150		$^{\circ}C$
Storage Temperature Range	$T_{stg}$	- 40 to + 150		$^{\circ}C$
Mounting torque		0.5	Recommended value	N.m

### Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	$I_{RM}$	$T_j= 25^{\circ}C, V_{RM}= V_{RRM}$	-	-	30	$\mu A$
Peak Forward Voltage	$V_{FM}$	$T_j= 25^{\circ}C, I_{FM}= 10A$	-	-	1.8	V
Reverse Recovery Time	trr	$I_{FM}= 10A,$ $-di/dt= 50 A/\mu s, T_a= 25^{\circ}C$	-	-	50	ns
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	-	-	4	$^{\circ}C/W$

GSF10A60B OUTLINE DRAWING (Dimensions in mm)



Single chip

